

**2N3250, A (SILICON)**

**2N3251, A**

2N3250A, 2N3251A JAN

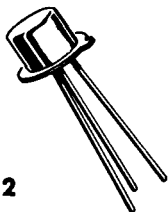
2N3250,A, 2N3251,A HI-REL



$V_{CEO} = 40-60 \text{ V}$

$I_C = 200 \text{ mA}$

$f_T = 250-300 \text{ MHz}$



PNP silicon annular transistors for high-speed switching and amplifier applications.

Collector connected to case

**CASE 22**  
(TO-18)

**MAXIMUM RATINGS**

Rating	Symbol	2N3250 2N3251	2N3250A 2N3251A	Unit
Collector-Base Voltage	$V_{CB}$	50	60	Vdc
Collector-Emitter Voltage	$V_{CEO}$	40	60	Vdc
Emitter-Base Voltage	$V_{EB}$	5		Vdc
Collector Current	$I_C$	200		mAdc
Total Device Dissipation @ 25°C Case Temperature Derating Factor Above 25°C	$P_D$	1.2 6.9		Watts mW/°C
Total Device Dissipation @ 25°C Ambient Temperature Derating Factor Above 25°C	$P_D$	0.36 2.06		Watts mW/°C
Junction Operating Temperature	$T_J$	200		°C
Storage Temperature Range	$T_{stg}$	-65 to +200		°C
Thermal Resistance	$\theta_{JA}$	0.49		°C/mW
	$\theta_{JC}$	0.15		°C/mW